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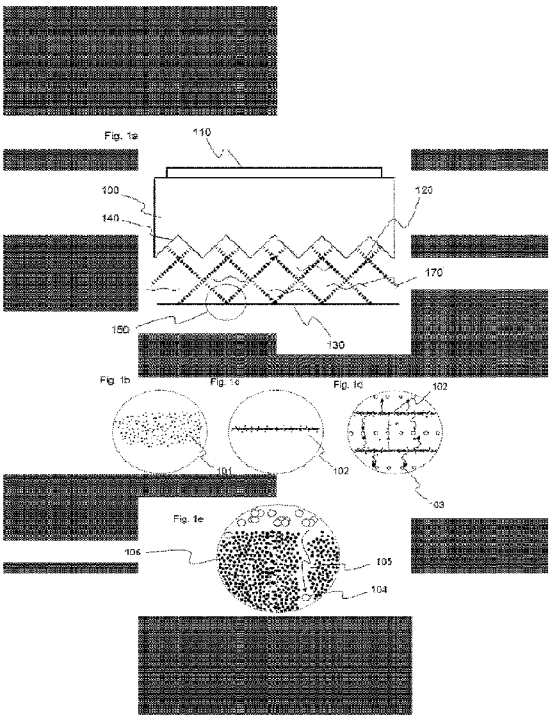
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(54) Title: IMPROVED ULTRASONIC CLEANING METHOD AND APPARATUS



(57) Abstract: A device and method for treating the surface of a semiconductor wafer provides a treatment fluid in the form of a dispersion of gas bubbles in a treatment liquid generated at acoustic pressures less than those required to induce cavitation in the treatmentliquid. A resonator supplies ultrasonic or megasonic energy to the treatment fluid and is configured to create aninterference pattern inthe treatment fluid comprising regions of pressure amplitude minima and maxima at an interface of the treatment fluid and the semiconductor wafer.

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